

E band MMIC SP8T Schottky Diode

E-SP8T-7681 Previously named CO-E1401504

GaAs Diode SP8T, 76-81 GHz

Overview

E-SP8T-7681 is a SP8T Schottky diode based switch that covers frequencies from 76GHz to 81GHz with very low loss (<5dB) when closed and high isolation (>20dB) when open. By using specialist matching circuitry, this MMIC provides an excellent match to 50ohm, even when the branch arm is open which allows ease of integration into complex multipath systems.

All bond pads and the die backside are gold plated. The MMIC is compatible with conventional die attach methods, as well as thermo-compression and thermosonic wire bonding, making it ideal for MCM and hybrid microcircuit applications. All data shown herein is provisional and is measured with the chip in a 50 Ohm environment and contacted with RF probes.

Features

- 76 - 81 GHz.
- < 5 dB insertion loss.
- > 20 dB isolation.
- > 10 dB return loss.
(Open or Closed)

Applications

- Millimeter-wave imaging.
- High resolution radar.
- Sensing.
- P2P communications;short haul/
high capacity/low interference
links.
- Medical.
- Automotive radar.

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Specification Overview

| Parameter | Min. | Typ. | Max. | Units | Notes |
|----------------------|------|------|------|-------|---|
| Frequency | 76 | | 81 | GHz | Biased at 0.81V, 10mA closed Biased at -1.2V, 0mA open |
| Insertion Loss | 5 | 4.5 | | dB | |
| Isolation | 20 | 25 | | dB | |
| Return Loss (Open) | 10 | | | dB | |
| Return Loss (Closed) | 10 | | | dB | |
| Closed Voltage | | 0.81 | | V | |
| Open Voltage | | -1.2 | | V | |
| Closed Current | | 10 | | mA | RFOUT1, RFOUT8 |
| | | 7 | | mA | RFOUT2, RFOUT7 |
| | | 7 | | mA | RFOUT3, RFOUT6 |
| | | 8 | | mA | RFOUT4, RFOUT5 |
| Open Current | | 0 | | mA | |

Notes

The tests indicated have all been performed with 100pF de-coupling capacitors on all bias pads. All tests are carried out at 25°C.

Absolute Maximum Ratings

| Parameter | Rating |
|-----------------------|-----------------|
| Control Voltage | -2 to +1.5V |
| RF Power | 22 dBm |
| Storage Temperature | -65°C to +175°C |
| Channel Temperature | +175°C |
| Operating Temperature | -40°C to +85°C |



ESD (electrostatic discharge) sensitive device. Charged devices and circuit boards can discharge without detection. Although this product features proprietary protection circuitry, damage may occur on devices subjected to ESD. Proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

Measured Performance Data

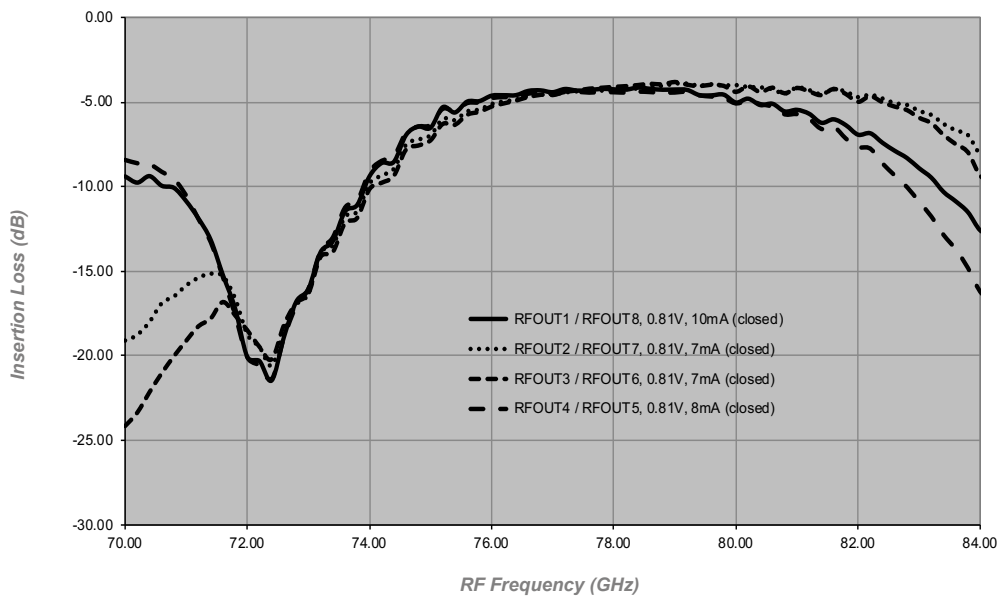


Figure 1
 Insertion Loss
 (all other branches open)

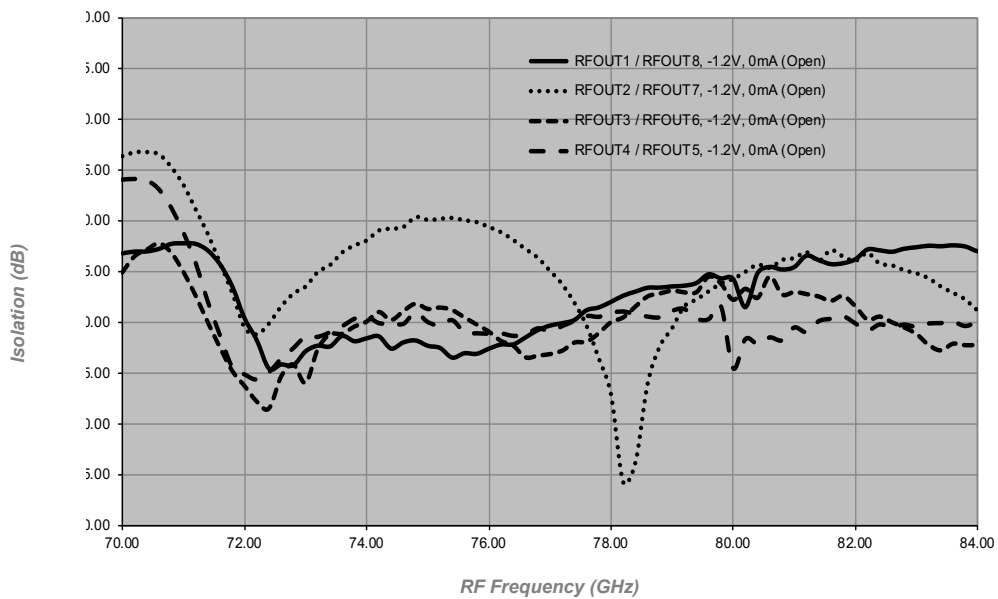


Figure 2
 Isolation
 (one other branch closed)

Measured Performance Data

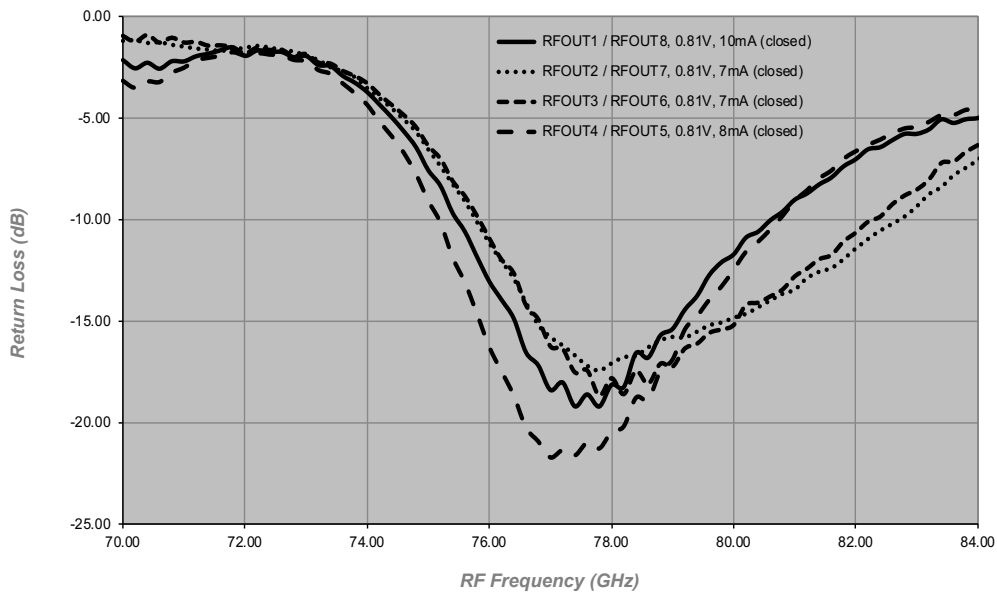


Figure 3
 Common Port Return Loss
 (all other branches open)

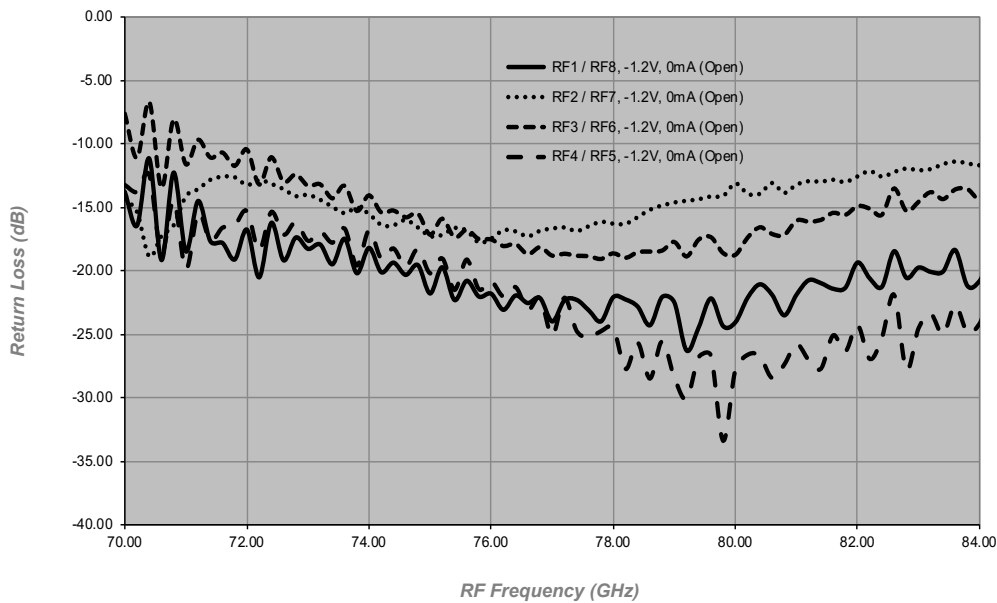
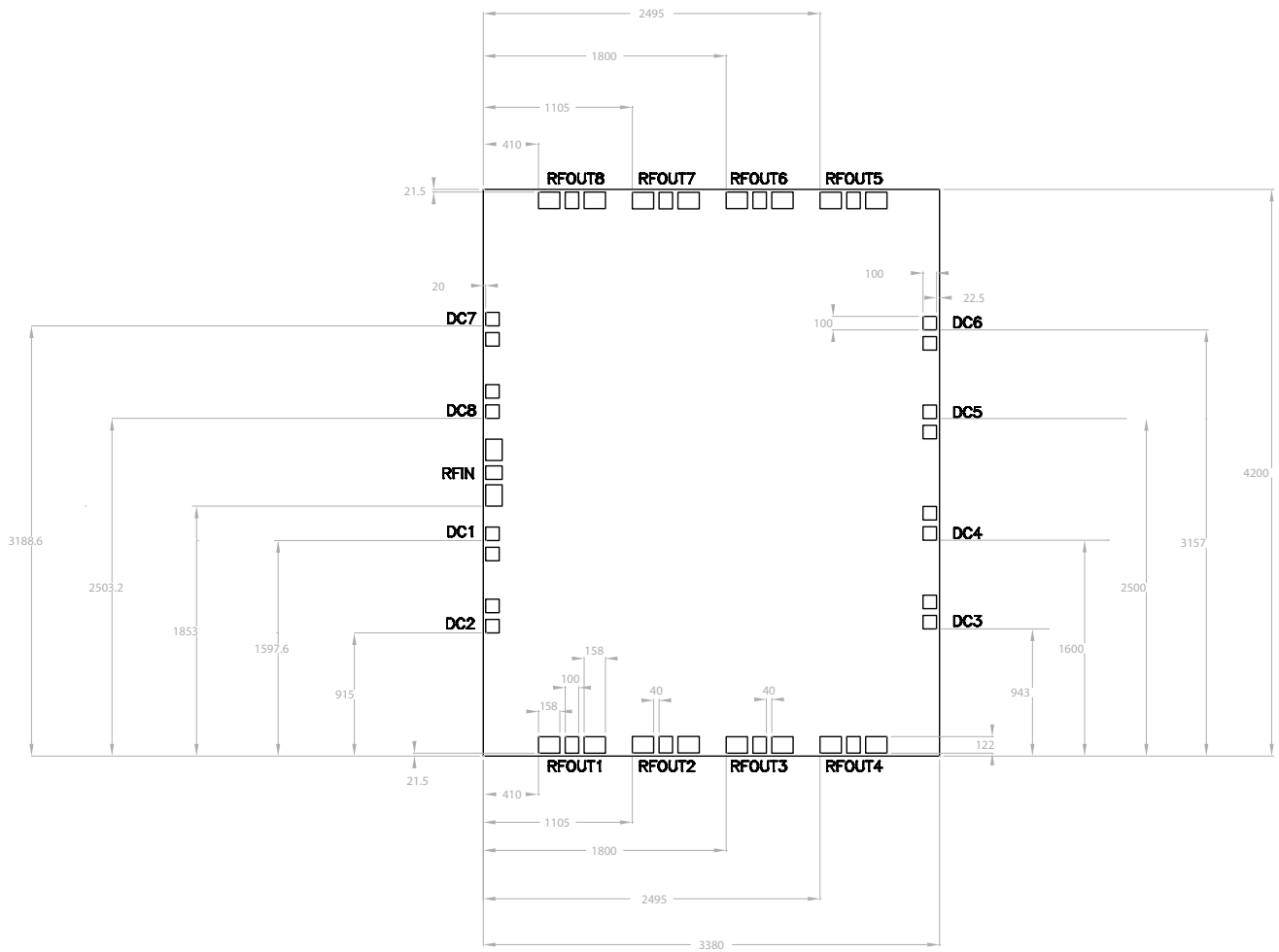


Figure 4
 Open Port Return Loss
 (one other branch closed)

Outline Drawing

Die Packing Information
All die are delivered using gel-paks unless otherwise requested.



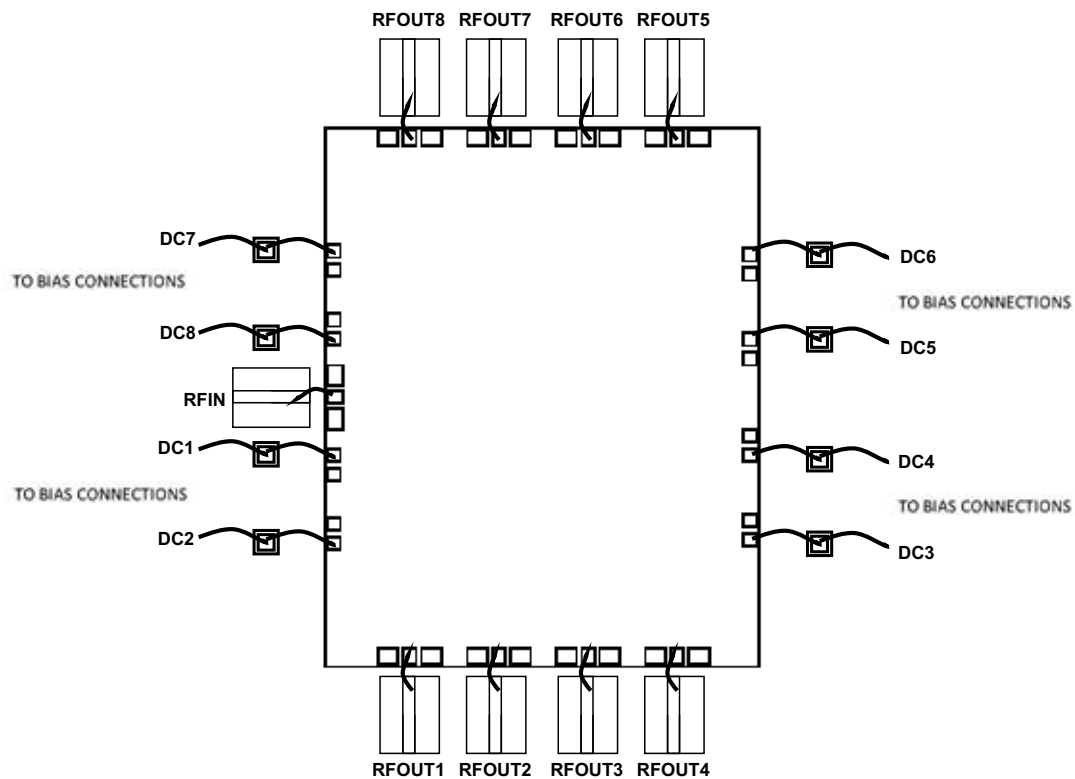
Notes

1. All dimensions are in μm.
2. RF bond pads are 122 x 100μm.
3. All DC bond pads are 100μm square.
4. Gold backside metalisation.
5. Backside metal is ground.
6. Die thickness is 100μm

Pad Descriptions

| Name | Description |
|---------------|---|
| RFIN | Common RF input pad. This pad is ac coupled. |
| RFOUTX | RF output pad for branch X. This pad is ac coupled. |
| DCX | This is DC control voltage pad for branch X. |
| BOTTOM | The die backside must be connected to RF/dc ground. |

Connection Configurations



General Notes on Assembly

Die should be mounted on conductive material such as gold-plated metal to provide a good ground and suitable heat sink, if necessary.

1. Attaching the die using Au/Sn preforms is preferable. The Eutectic melt for Au/Sn occurs at approximately 280°C so the die (plus mount and preform) is initially heated up to 180°C and then it is heated for approximately 10 seconds to 280°C using a nitrogen heat gun. The device will survive 10 seconds at this temperature. The static breakdown for GaAs devices is approximately 330°C.
2. Pure, dry nitrogen should be used as the heat source.
3. If the devices cannot be lifted/ placed by a vacuum device, then ESD die-lifting tweezers are preferable.
4. Supply lines should be decoupled with 100pF capacitors. Larger planar capacitors could be used if available.
5. Aluminium wire must not be used.

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